

# Central<sup>TM</sup> Semiconductor Corp.

145 Adams Ave., Hauppauge, NY 11788 USA  
Phone (516) 435-1110 FAX (516) 435-1824

Manufacturers of World Class Discrete Semiconductors

CMPFJ310

SURFACE MOUNT  
SILICON N-CHANNEL JFET

SOT-23 CASE

## DESCRIPTION

The CENTRAL SEMICONDUCTOR CMPFJ310 type is a epoxy molded N-Channel Silicon Junction Field Effect Transistor manufactured in an SOT-23 case, designed for VHF/UHF amplifier applications.

Marking code is 6T.

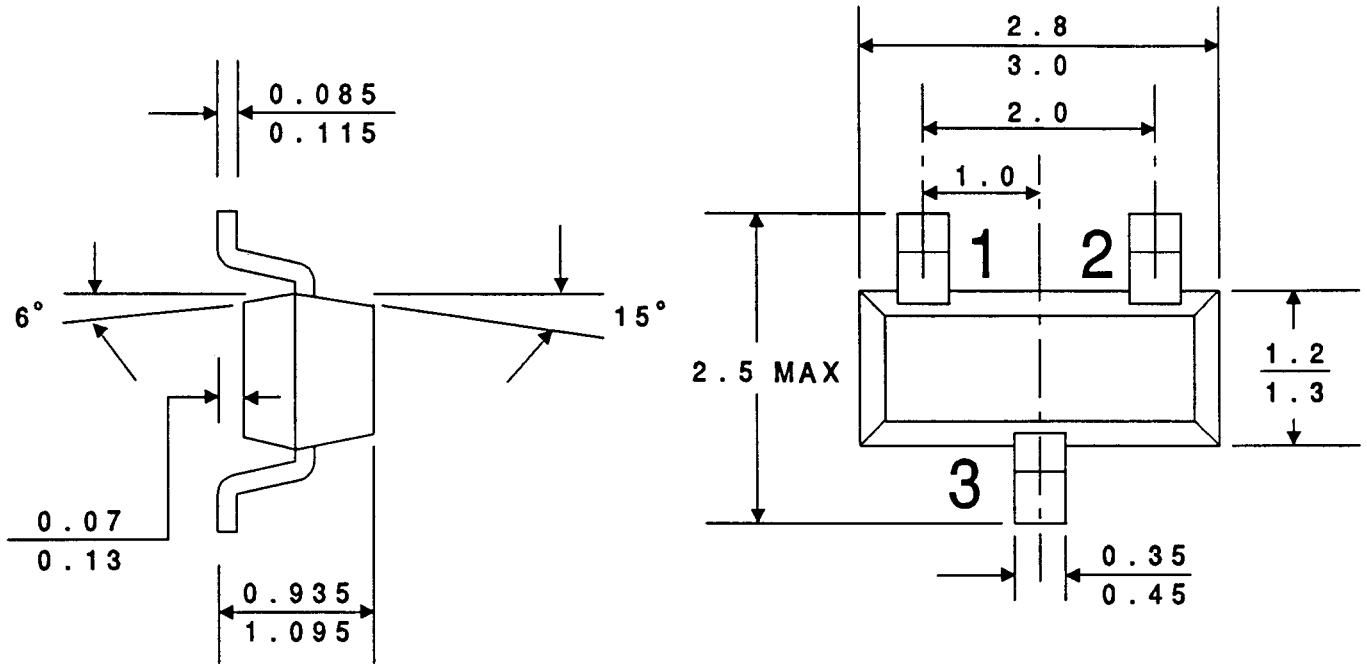
## MAXIMUM RATINGS (T<sub>A</sub> = 25°C)

	SYMBOL		UNITS
Drain-Source Voltage	V <sub>DS</sub>	25	V
Gate-Source Voltage	V <sub>GS</sub>	25	V
Gate Current	I <sub>G</sub>	10	mA
Power Dissipation	P <sub>D</sub>	350	mW
Operating and Storage			
Junction Temperature	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C
Thermal Resistance	θ <sub>JA</sub>	357	°C/W

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I <sub>GSS</sub>	V <sub>GS</sub> = 15V			1.0	nA
I <sub>GSS</sub>	V <sub>GS</sub> = 15V, T <sub>A</sub> = 125°C			1.0	µA
I <sub>DSS</sub>	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0	24		60	mA
BV <sub>GS</sub>	I <sub>G</sub> = 1.0µA	25			V
V <sub>GS(off)</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1.0nA	2.0		6.5	V
V <sub>GS(f)</sub>	I <sub>G</sub> = 1.0mA, V <sub>DS</sub> = 0			1.0	V
Y <sub>fs</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 10mA, f = 1.0kHz	8.0		18	mmhos
Y <sub>os</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 10mA, f = 1.0kHz			250	µmhos
C <sub>iss</sub>	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 0, f = 1.0MHz			5.0	pF
C <sub>rss</sub>	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 0, f = 1.0MHz			2.5	pF
$\bar{e}_n$	V <sub>DS</sub> = 10V, I <sub>D</sub> = 10mA, f = 100Hz		10		nV/√Hz

All Dimensions in mm.



LEAD CODE:

MARKING CODE: 6T

- 1) SOURCE
- 2) DRAIN
- 3) GATE